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Docket No. 0819-0425

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

)

Haruko INOUE et al.

) Group Art Unit: 2811

Serial No. 09/666,156

) Examiner: S. Loke

Filed: September 19, 2000

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For: HIGH-VOLTAGE MOS

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TRANSISTOR AND METHOD

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FOR FABRICATING THE SAME

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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on 3/21/02

RESPONSE TO ELECTION REQUIREMENT

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the election requirement in the Office Action of February 20, 2002, Applicants hereby elect without traverse the Group I claims - that is, claims 1-7, drawn to a semiconductor device.

Examination on the merits is requested.

Respectfully submitted,


Eric J. Robinson
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